L	Hits	Search Text	TDB	I mima manus
Number	hits	Search lext	DB	Time stamp
1	585	(kozo near2 nakamura or toshiaki near2	USPAT;	2004/07/29
		saishoji or hirotaka near2 nakajima or	US-PGPUB;	11:25
		masashi near2 nishimura or toshirou near2	EPO; JPO;	
		kotooka near2 yoshiyuki near2 shimanuki).in.	DERWENT;	
2	35	,,	IBM_TDB USPAT;	2004/07/20
~		saishoji or hirotaka near2 nakajima or	US-PGPUB;	2004/07/29
		masashi near2 nishimura or toshirou near2	EPO; JPO;	11.25
	1	kotooka near2 yoshiyuki near2	DERWENT;	
		shimanuki).in.) and heat near2 treat\$5	IBM_TDB	
3	0	(\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	USPAT;	2004/07/29
	1	saishoji or hirotaka near2 nakajima or	US-PGPUB;	11:26
		masashi near2 nishimura or toshirou near2 kotooka near2 yoshiyuki near2	EPO; JPO;	
		shimanuki).in.) and heat near2 treat\$5	DERWENT; IBM TDB	
		and ramp\$5 near2 rate	IDM_IDD	
-	20		USPAT;	2002/05/17
			US-PGPUB;	13:34
1			EPO; JPO;	
			DERWENT;	
_	17	"5968264"	IBM_TDB USPAT;	2002/05/17
	'	3500204	US-PGPUB;	2002/05/17 13:35
1			EPO; JPO;	13.33
			DERWENT;	
			IBM_TDB	
-	16	"5788763"	USPAT;	2002/05/17
			US-PGPUB;	13:58
			EPO; JPO; DERWENT;	
	1		IBM TDB	
i –	373	czochralski and (temperature adj	USPAT;	2002/05/17
		gradient) and (speed or velocity)	US-PGPUB;	14:00
			EPO; JPO;	
-			DERWENT;	
 _	332	czochralski and (temperature adj	IBM_TDB USPAT;	2002/05/17
		gradient) same (speed or velocity or	US-PGPUB;	14:32
		rate)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	606	memc.as.	USPAT;	2002/05/17
			US-PGPUB; EPO; JPO;	14:32
			DERWENT;	
			IBM_TDB	
_	174	memc.as. and czochralski	USPAT;	2002/05/17
			US-PGPUB;	14:41
			EPO; JPO;	
			DERWENT; IBM TDB	
_	53	memc.as. and czochralski and gradient	USPAT;	2003/05/04
			US-PGPUB;	14:43
		·	EPO; JPO;	
			DERWENT;	
_	873	wafer and (anneal\$3 or (heat adj treat\$4)	IBM_TDB USPAT;	2002/05/17
	0,3	or (rapid adj thermal) or RTA or RTP or	US-PGPUB;	16:27
		PTP) and czochralski	EPO; JPO;	
			DERWENT;	
	F 0.0		IBM_TDB	
_	598	wafer and (anneal\$3 or (heat adj treat\$4)	USPAT;	2002/05/17
		or (rapid adj thermal) or RTA or RTP or PTP) same temperature and czochralski	US-PGPUB; EPO; JPO;	16:30
	Į.	111, 23mo competadate and ezocnitatori	DERWENT;	
	· .		IBM TDB	

-	256		USPAT;	2003/12/30
		(si or silicon) near2 (wafer or	US-PGPUB;	15:42
1		substrate) same temperature near10 ("700"	EPO; JPO;	
1		or "800" or "650" or "750" or "900" or	DERWENT;	
	38	(2000)	IBM_TDB	2002/10/20
_	36	(anneal\$ or heat\$3 near2 treat\$) near15 (si or silicon) near2 (wafer or	USPAT;	2003/12/30
		substrate) same temperature near10 ("700"	US-PGPUB;	15:47
		or "800" or "650" or "750" or "900" or	EPO; JPO; DERWENT;	
		"950") same rate	IBM TDB	
_	15	· · · · · · · · · · · · · · · · · · ·	USPAT;	2003/12/30
	1	(si or silicon) near2 (wafer or	US-PGPUB;	15:47
		substrate) same temperature same rate	EPO; JPO;	13.17
		near2 less	DERWENT;	
	•		IBM TDB	
-	248	((Thermal or temperature) adj gradient)	USPAT;	2004/01/05
		near5 (speed or rate) and czochralski	US-PGPUB;	10:04
		· -	EPO; JPO;	
	1		DERWENT;	
1			IBM TDB	
-	2	5567399.pn.	USPĀT;	2004/01/05
			US-PGPUB;	10:32
			EPO; JPO;	
			DERWENT;	
	25.5	(4)	IBM_TDB	
1 -	251	(thermal or temperature) near2 gradient	USPAT;	2004/01/05
		near5 (speed or rate) and czochralski	US-PGPUB;	10:34
			EPO; JPO;	
			DERWENT;	
- <u>-</u>	145	(thermal or temperature) near2 gradient	IBM_TDB	2004/01/05
	143	near5 pull\$3 near3 (speed or rate) and	USPAT; US-PGPUB;	2004/01/05 11:08
		czochralski	EPO; JPO;	11:08
İ		CZOCIII al Ski	DERWENT;	
			IBM TDB	
_	1	9315882.pn.	USPAT;	2004/01/05
			US-PGPUB;	11:08
		·	EPO; JPO;	
			DERWENT;	
1			IBM TDB	
-	2	09315882.pn.	USPAT;	2004/01/05
			US-PGPUB;	11:08
1			EPO; JPO;	
			DERWENT;	
		, , , , , , , , , , , , , , , , , , ,	IBM_TDB	
-	5663	heat near2 treat\$4 same (si or silicon)	USPAT;	2004/07/19
		near5 (single near2 crystal\$5 or wafer)	US-PGPUB;	17:05
			EPO; JPO;	
	1.		DERWENT;	
_	1655	heat near2 treat\$4 near10 temperature	IBM_TDB	2004/07/10
1	1655	same (si or silicon) near5 (single near2	USPAT; US-PGPUB;	2004/07/19
		crystal\$5 or wafer)	EPO; JPO;	17.03
	1	orizontia or marori	DERWENT;	
-			IBM TDB	
-	113	heat near2 treat\$4 near10 temperature	USPAT;	2004/07/19
		near10 (ramp\$4 or rate) same (si or	US-PGPUB;	17:43
		silicon) near5 (single near2 crystal\$5 or	EPO; JPO;	
-		wafer)	DERWENT;	
			IBM TDB	
-	2	"07165495"	USPAT;	2004/07/19
		·	US-PGPUB;	17:14
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	182	heat_near2 treat\$4 near10 temperature	USPĀT;	2004/07/19
		near5 low same (si or silicon) near5	US-PGPUB;	17:49
	_{st}	(single near2 crystal\$5 or wafer)	EPO; JPO;	
			DERWENT;	
	i. #		IBM TDB	

	,	<u> </u>		
-	15	heat near2 treat\$4 near10 temperature	USPAT;	2004/07/20
		near5 initial\$5 same (si or silicon)	US-PGPUB;	09:08
		near5 (single near2 crystal\$5 or wafer)	EPO; JPO;	
		·	DERWENT;	
			IBM_TDB	
_	17	heat_near2 treat\$4 near10 temperature	USPAT;	2004/07/20
`l		near5 start\$5 same (si or silicon) near5	US-PGPUB;	09:23
		(single near2 crystal\$5 or wafer)	EPO; JPO;	
			DERWENT;	
]	_		IBM_TDB	1
_	195	(sueoka near2 koji or koike near2 yasuo	USPAT;	2004/07/20
i		or sadamitsu near2 shinsuke).in.	US-PGPUB;	09:24
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	i
-	2	((sueoka near2 koji or koike near2 yasuo	USPAT;	2004/07/20
		or sadamitsu near2 shinsuke).in.) and	US-PGPUB;	09:25
		(start\$5 or initial\$5 or starting	EPO; JPO;	
		initiat\$5) near6 temperature	DERWENT;	
			IBM_TDB	
-	26	((sueoka near2 koji or koike near2 yasuo	USPAT;	2004/07/29
		or sadamitsu near2 shinsuke).in.) and	US-PGPUB;	11:23
		temperature same (heat near2 treat\$5 or	EPO; JPO;	
		anneal\$5) same (si or silicon) near5	DERWENT;	
		(substrate or wafer)	IBM TDB	